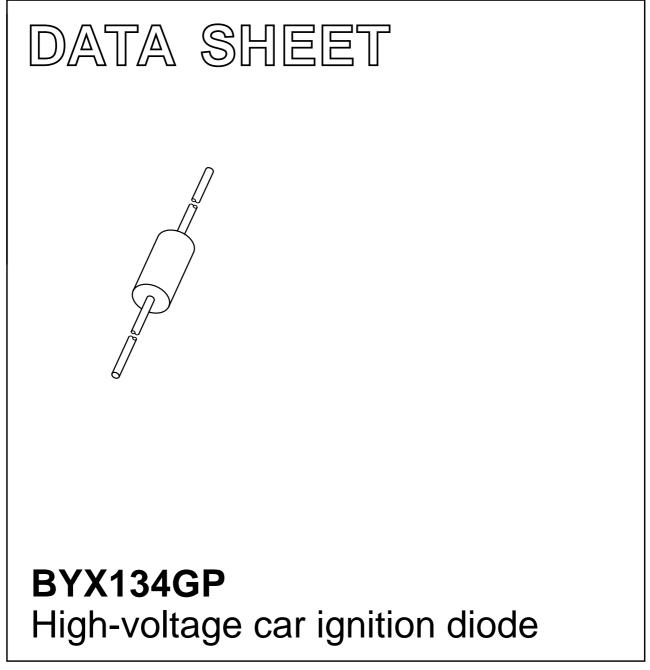
## DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1998 Dec 04 2001 Oct 02



### **Product specification**

### High-voltage car ignition diode

### BYX134GP

### FEATURES

- · Glass passivated
- High maximum operating temperature
- Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability.

#### APPLICATIONS

- · Car ignition systems
- Automotive applications with extreme temperature requirements.

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL             | PARAMETER                           | CONDITIONS   | MIN. | MAX. | UNIT |
|--------------------|-------------------------------------|--|------|------|------|
| V <sub>RRM</sub>   | repetitive peak reverse voltage     |  | -    | 4    | kV   |
| V <sub>RWM</sub>   | crest working reverse voltage       |  | -    | 4    | kV   |
| I <sub>F(AV)</sub> | average forward current             |  | -    | 50   | mA   |
| I <sub>FRM</sub>   | repetitive peak forward current     |  | -    | 500  | mA   |
| I <sub>RSM</sub>   | non-repetitive peak reverse current | t = 100 $\mu$ s triangular pulse;<br>T <sub>j max</sub> prior to surge | -    | 50   | mA   |
| T <sub>stg</sub>   | storage temperature                 |  | -65  | +175 | °C   |
| Tj                 | junction temperature                | continuous   | -    | 175  | °C   |

### CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

| SYMBOL             | PARAMETER                           | CONDITIONS                                  | MIN. | MAX. | UNIT |
|--------------------|-------------------------------------|---|------|------|------|
| V <sub>F</sub>     | forward voltage                     | I <sub>F</sub> = 10 mA                      | 5    | 7    | V    |
| V <sub>(BR)R</sub> | reverse avalanche breakdown voltage | I <sub>R</sub> = 100 μA                     | 5.5  | 7.5  | kV   |
| I <sub>R</sub>     | reverse current                     | $V_R = V_{RWMmax}$ ; $T_j = 175 \ ^\circ C$ | _    | 30   | μA   |

### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                                   | CONDITIONS                                  | VALUE | UNIT |
|---------------------|---|---|-------|------|
| R <sub>th j-a</sub> | thermal resistance from junction to ambient | $T_{amb} = T_{leads}$ ; lead length = 10 mm | 100   | K/W  |

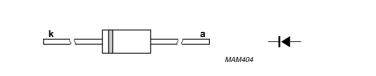
#### DESCRIPTION

Rugged glass package, using a high temperature alloyed construction.

The SOD107A is hermetically sealed and fatigue free as coefficients of

expansion of all used parts are matched.

The package is designed to be used in an insulating medium such as resin, oil or SF6 gas.

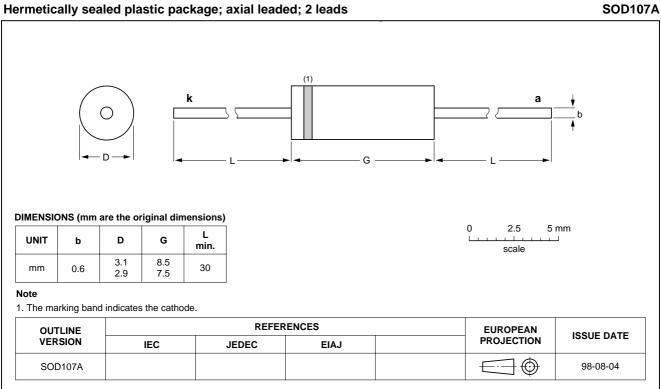


Cathode indicated by light blue band.

Fig.1 Simplified outline (SOD107A) and symbol.

### BYX134GP

### PACKAGE OUTLINE



BYX134GP

#### DATA SHEET STATUS

| DATA SHEET STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITIONS  |
|----------------------------------|----------------------------------|--|
| Objective data                   | Development                      | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.  |
| Preliminary data                 | Qualification                    | This data sheet contains data from the preliminary specification.<br>Supplementary data will be published at a later date. Philips<br>Semiconductors reserves the right to change the specification without<br>notice, in order to improve the design and supply the best possible<br>product.                                     |
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#### Notes

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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